Revision 1.02

GAIN CHIPS AR coated Fabry-Perot Laser

General Product Information

Product	Application
tunable 760 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	covering wavelengths between
sealed SOT Housing	752 and 772 nm
Monitor Diode	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	Ts	°C	-40		85
Operational Temperature at Case	T _c	°C	-20		50
Forward Current	I _F	mA			200
Reverse Voltage	V _R	V			0
Output Power (ex-cavity)	P _{opt}	mW			100

Recommended Operational Conditions

Parameter	Symbol	Unit	min	tvp	max
Operational Temperature at Case	T _C	°C	15	76	40
Forward Current	I _F	mA			180

Characteristics ex-cavity at T_c25°C, at BOL under recommended working condition

λ_{c} nm	760)
λ _{tun} nm	752	772
P _{opt} mW	80	
	TM	
	TEM	I ₀₀
	λ _{tun} nm	λ _{tun} nm 752 Popt mW 80 TM

Measurement Conditions / Comments

Stess in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Measurement Conditions / Comments

Measurement Conditions / Comments The actual achieved wavelength and power are strongly influenced by the external cavity. eyP gives no guarantee on these parameters.

E field perpendicular to Pin 2 - Pin 3 - plane Fundamental Mode

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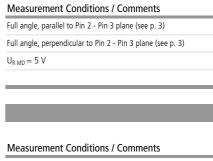
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Amplified Spontaneous Emission (ASE)					
without external cavity					
Parameter	Symbol	Unit	min	typ	max
Divergence parallel (FWHM)	$\Theta_{ }$	0		10	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		28	
Monitor Detector Responsivity	I _{mon} / P _{ASE}	µA/mW	1		40

Chip Parameter

Parameter	Symbol	Unit	min	typ	max
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R _{ff}			3·10 ⁻⁴	1·10 ⁻³



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2019-03-01

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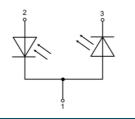
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Symbol	Unit	min	typ	max
h	mm	3.50	3.65	3.70
R	mm			0.12
L _{PIN}	mm		14	
	h R	h mm R mm	h mm 3.50 R mm	h mm 3.50 3.65 R mm

Measurement Conditions / Comments reference plane: top side of TO header reference: center of outer diameter of header

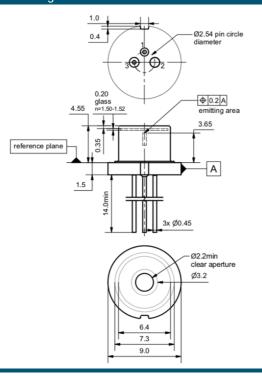
Package Pinout

- 1 Laser Diode Anode, Monitor Diode Cathode, Case
- 2 Photo Diode Anode
- 3 Laser Diode Cathode





Package Drawings





AIZ-16-0421-1517

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TOPTICA

Typical Measurement Results ex-cavity 0 180 120 = 81 mW ASE 752,4 nm 755,5 nm 757.6 nm 760,0 nm 762,5 nm ASE -10 160 cw-power (0. order) in mW 752,40 nm 755,00 nm 757,60 nm 100 -20 140 760,00 nm 762,50 nm 765,00 nm 765,0 nm -30 120 80 767,50 nm 767,5 nm 770,00 nm 770,0 nm 771,80 nm -40 771,8 nm 100 60 -50 80 40 -60 60 -70 40 20 -80 20 -90 0 0. 750 60 80 100 120 140 160 180 200 730 740 760 770 780 790 40 current in mA wavelength in nm

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode. The chip should be protected against moisture. A water vapor content below 5000 ppm is recommended for applications with high reliability requirements.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



Complies with 21 CFR 1040.10 and 1040.40

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